



40V Dual N-Channel Enhancement Mode MOSFET

Voltage

40 V

Current

14 A

Features

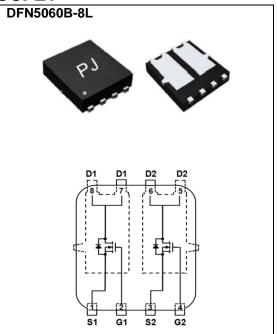
- $R_{DS(ON)}$, $V_{GS}@10V$, $I_D@8A<33m\Omega$
- $R_{DS(ON)}$, $V_{GS}@4.5V$, $I_{D}@4A<42m\Omega$
- High switching speed
- Improved dv/dt capability
- Low reverse transfer capacitance
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

• Case: DFN5060B-8L Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.0035 ounces, 0.092 grams



Maximum Ratings and Thermal Characteristics (T_A=25 °C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V_{DS}	40	.,,	
Gate-Source Voltage		V_{GS}	<u>+</u> 20	V	
Continuous Drain Current (Note 4)	T _C =25°C	I _D	14		
	T _C =100°C		9	Α	
Pulsed Drain Current (Note 1)	T _C =25°C	I _{DM}	56		
Power Dissipation	T _C =25°C	Po	12	10/	
	T _C =100°C		4.8	W	
Continuous Drain Current (Note 4)	T _A =25°C	I _D	5		
	T _A =70°C		4	Α	
Power Dissipation	T _A =25°C	Po	1.7		
	T _A =70°C		1.1	W	
Operating Junction and Storage Temperature Range		T_{J} , T_{STG}	-55~150	°C	
Typical Thermal Resistance (Note 4,5)	Junction to Case	$R_{\theta JC}$	10.4	°C/W	
	Junction to Ambient	$R_{\theta JA}$	73.5		

Limited only By Maximum Junction Temperature





Electrical Characteristics (T_A=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250uA	40	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=250uA$	1.2	1.8	2.5	
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =10V, I _D =8A	-	27	33	mΩ
Drain-Source On-State Resistance	R _{DS(on)}	V_{GS} =4.5V, I_D =4A	-	35	42	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =40V, V _{GS} =0V	-	-	1.0	uA
Gate-Source Leakage Current	I_{GSS}	V _{GS} = <u>+</u> 20V, V _{DS} =0V	-	ı	<u>+</u> 100	nA
Dynamic (Note 6)						
Total Gate Charge	Q_{g}	V _{DS} =20V, I _D =5A, V _{GS} =4.5V ^(Note 3)	-	4.4	-	nC
Gate-Source Charge	Q_{gs}		-	1.3	-	
Gate-Drain Charge	Q_{gd}		-	1.7	-	
Input Capacitance	Ciss	V _{DS} =25V, V _{GS} =0V,	-	425	-	pF
Output Capacitance	Coss		-	48	-	
Reverse Transfer Capacitance	Crss	f=1MHZ	-	36	-	
Turn-On Delay Time	td _(on)		-	9.4	-	
Turn-On Rise Time	t _r	V_{DD} =20V, I_{D} =1A, V_{GS} =4.5V, R_{G} =25 Ω (Note 3)	-	29	-	ns
Turn-Off Delay Time	td _(off)		-	21	-	
Turn-Off Fall Time	t _f		-	29	-	
Drain-Source Diode						
Maximum Continuous Drain-Source				-	14	А
Diode Forward Current	I _S		-			
Diode Forward Voltage	V _{SD}	I _S =1A, V _{GS} =0V	-	0.74	1	V

NOTES:

- 1. Pulse width<a>300us, Duty cycle<a>2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$ =150°C. Ratings are based on low frequency and duty cycles to keep initial T_J =25°C.
- 4. The maximum current rating is package limited.
- 5. Rejah is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 6. Guaranteed by design, not subject to production testing.





TYPICAL CHARACTERISTIC CURVES

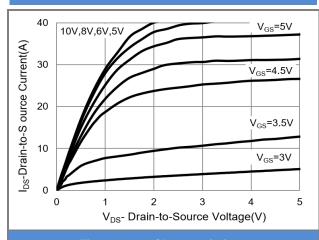


Fig.1 Output Characteristics

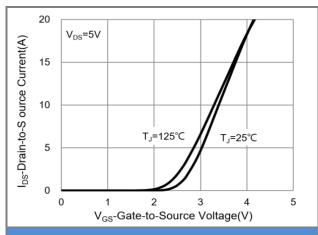


Fig.2 Transfer Characteristics

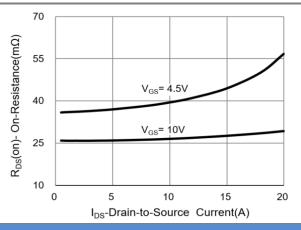


Fig.3 On-Resistance vs. Drain Current

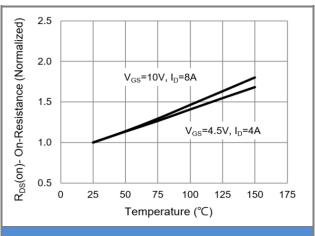


Fig.4 On-Resistance vs. Junction temperature

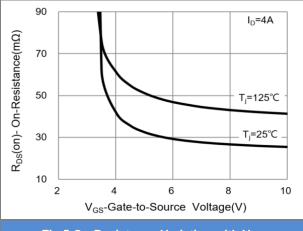


Fig.5 On-Resistance Variation with V_{GS}

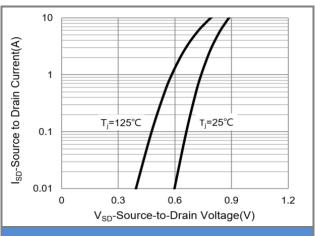


Fig.6 Source-Drain Diode Forward Voltage





TYPICAL CHARACTERISTIC CURVES

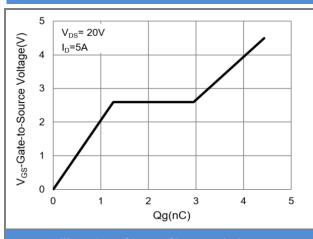


Fig.7 Gate-Charge Characteristics

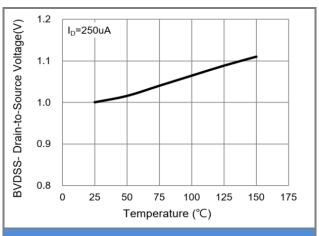


Fig.8 Breakdown Voltage Variation vs. Temperature

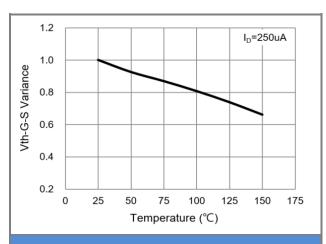


Fig.9 Threshold Voltage Variation with Temperature

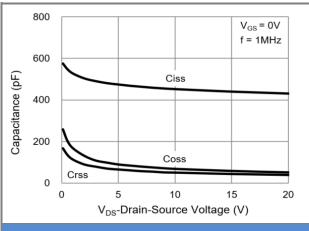
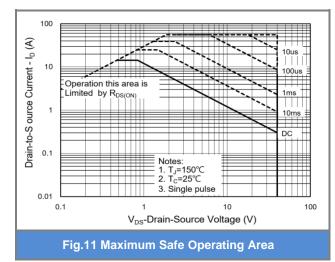


Fig.10 Capacitance vs. Drain-Source Voltage



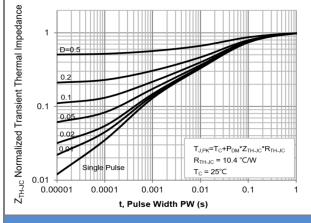


Fig.12 Normalized Transient Thermal Impedance

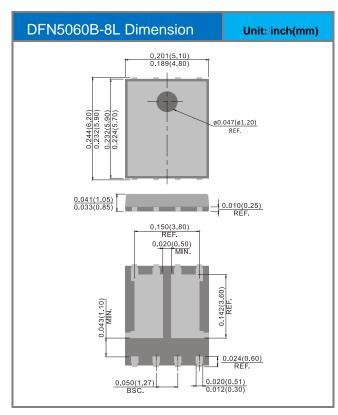


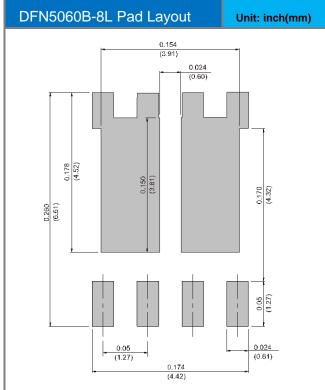


Part No Packing Code Version

Part No Packing Code	Package Type	Packing Type	Marking	Version	
PJQ5850_R2_00001	DFN5060B-8L	3000pcs / 13" reel	Q5850	Halogen free	

Packaging Information & Mounting Pad Layout









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